

## DUAL 2 TO 4 LINE DECODER 3 TO 8 LINE DECODER

- HIGH SPEED  
 $t_{PD} = 12 \text{ ns}$  (TYP.) AT  $V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION  
 $I_{CC} = 4 \mu\text{A}$  (MAX.) AT  $T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY  
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (MIN.)
- OUTPUT DRIVE CAPABILITY  
10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE  
 $|I_{OH}| = I_{OL} = 4 \text{ mA}$  (MIN.)
- BALANCED PROPAGATION DELAYS  
 $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE  
 $V_{CC}$  (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE  
WITH 54/74LS155

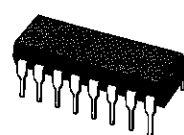
### DESCRIPTION

The M54/74HC155 is a high speed CMOS DUAL 2-TO-4 LINE DECODER fabricated in silicon gate C<sup>2</sup>MOS technology.

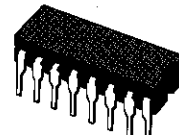
It has the same high speed performance of LSTTL combined with true CMOS low power consumption. It features dual 1-TO-4 line demultiplexers with individual strobe inputs (1G and 2G), individual data inputs (1C and 2C) and common binary address inputs (A and B).

When both decoders are enabled by the strobes, the inverted output of 1C data and non-inverted output of 2C data will be brought to the select output pins of each sections. A 1-TO-8 line demultiplexer can also be easily built up by providing a data signal to both 1C and 2C inputs; the output order from the msb is 1Y3, 1Y2, 1Y1, 1Y0, 2Y3, 2Y2, 2Y1, 2Y0. This device can be used as a 2-to-4 line decoder or a 3-to-8 line decoder when 1C is held high and 2C is held low.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.



**B1R**  
(Plastic Package)



**F1R**  
(Ceramic Package)



**M1R**  
(Micro Package)

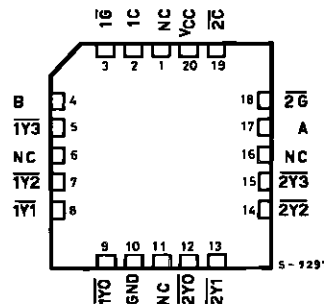
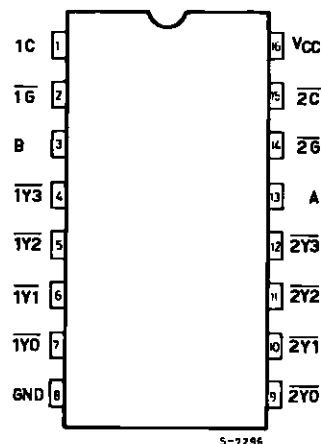


**C1R**  
(Chip Carrier)

### ORDER CODES :

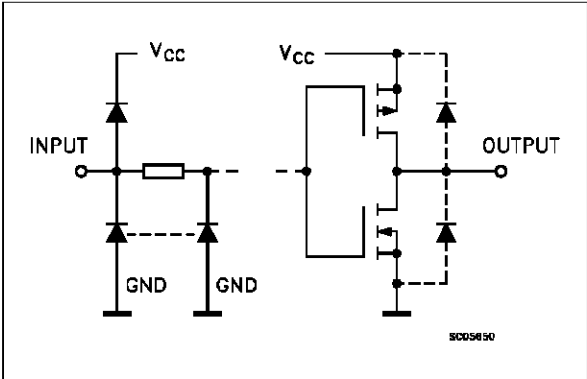
M54HC155F1R	M74HC155M1R
M74HC155B1R	M74HC155C1R

### PIN CONNECTIONS (top view)



NC =  
No Internal  
Connection

INPUT AND OUTPUT EQUIVALENT CIRCUIT



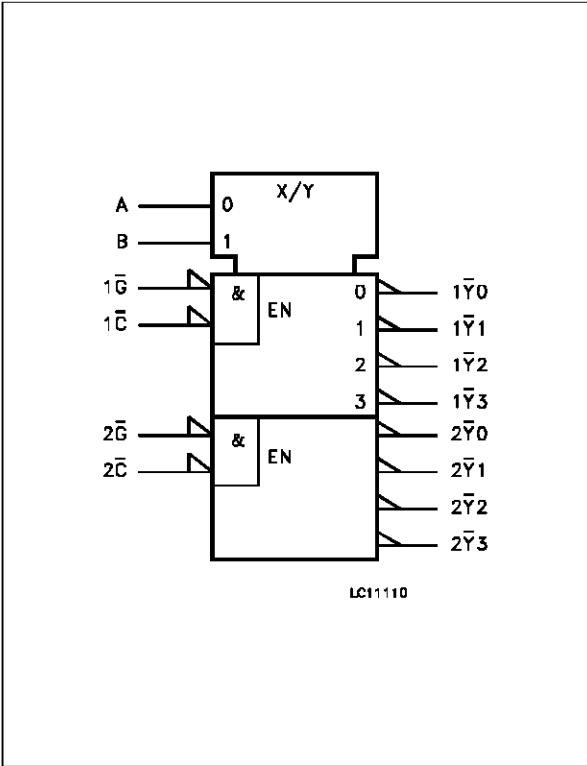
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 15	1C, $\overline{2C}$	Data Inputs
2, 14	1G, $\overline{2G}$	Strobe Inputs
3, 13	B, A	Common Data Inputs
7, 6, 5, 4	$\overline{1Y0}$ to $\overline{1Y3}$	Outputs
9, 10, 11, 12	$\overline{2Y0}$ to $\overline{2Y3}$	Outputs
8	GND	Ground (0V)
16	V <sub>CC</sub>	Positive Supply Voltage

TRUTH TABLE

INPUTS				OUTPUTS			
B	A	1G	1C	$\overline{1Y0}$	$\overline{1Y1}$	$\overline{1Y2}$	$\overline{1Y3}$
X	X	H	X	H	H	H	H
L	L	L	H	L	H	H	H
L	H	L	H	H	L	H	H
H	L	L	H	H	H	L	H
H	H	L	H	H	H	H	L
X	X	X	L	H	H	H	H

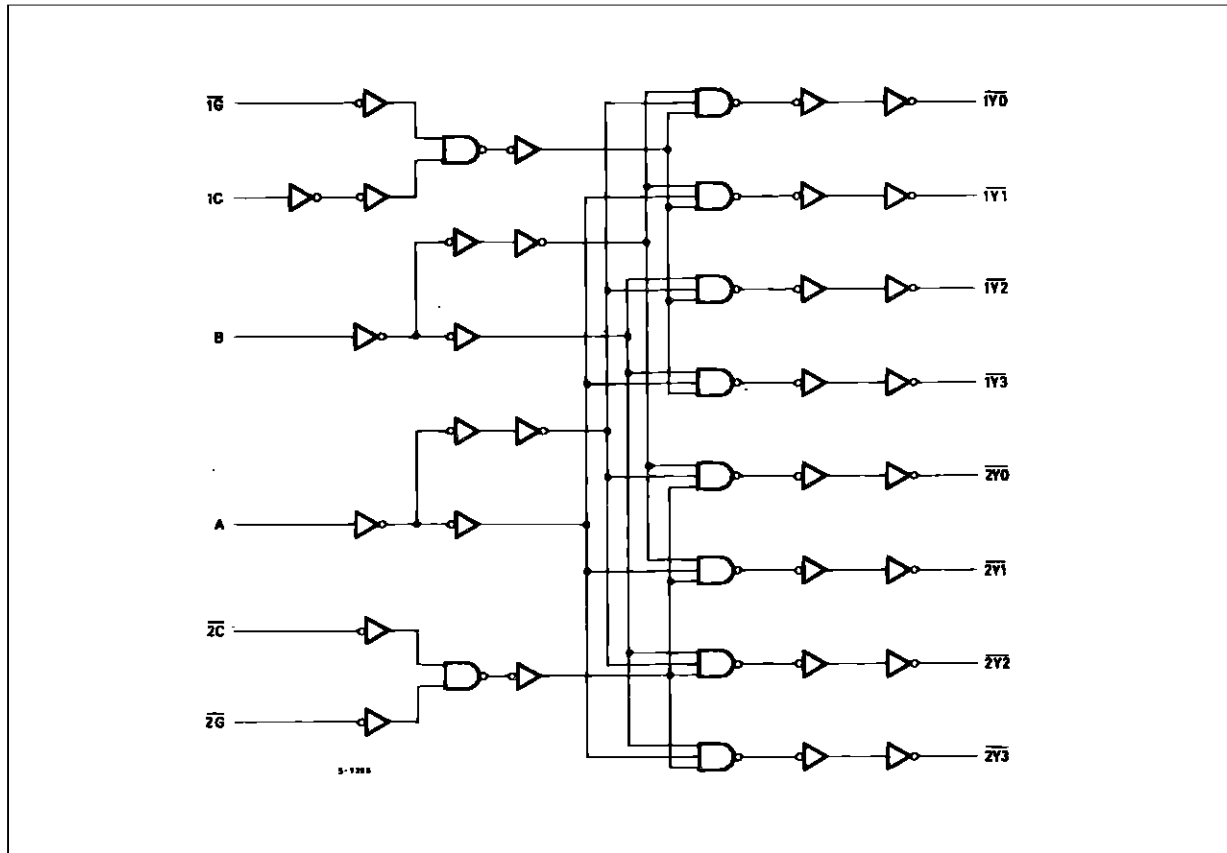
IEC LOGIC SYMBOL



TRUTH TABLE

INPUTS				OUTPUTS			
B	A	2G	2C	$\overline{2Y0}$	$\overline{2Y1}$	$\overline{2Y2}$	$\overline{2Y3}$
X	X	H	X	H	H	H	H
L	L	L	L	L	H	H	H
L	H	L	L	H	L	H	H
H	L	L	L	H	H	L	H
H	H	L	L	H	H	H	L
X	X	X	H	H	H	H	H

## LOGIC CIRCUIT



## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	-0.5 to +7	V
$V_I$	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_O$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$\pm 20$	mA
$I_{OK}$	DC Output Diode Current	$\pm 20$	mA
$I_O$	DC Output Source Sink Current Per Output Pin	$\pm 25$	mA
$I_{CC}$ or $I_{GND}$	DC $V_{CC}$ or Ground Current	$\pm 50$	mA
$P_D$	Power Dissipation	500 (*)	mW
$T_{stg}$	Storage Temperature	-65 to +150	$^{\circ}\text{C}$
$T_L$	Lead Temperature (10 sec)	300	$^{\circ}\text{C}$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(\*) 500 mW:  $\pm 65^{\circ}\text{C}$  derate to 300 mW by 10mW/ $^{\circ}\text{C}$ :  $65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	2 to 6	V
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature: <b>M54HC Series</b> <b>M74HC Series</b>	-55 to +125 -40 to +85	°C °C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> = 2 V	ns
		V <sub>CC</sub> = 4.5 V	
		V <sub>CC</sub> = 6 V	

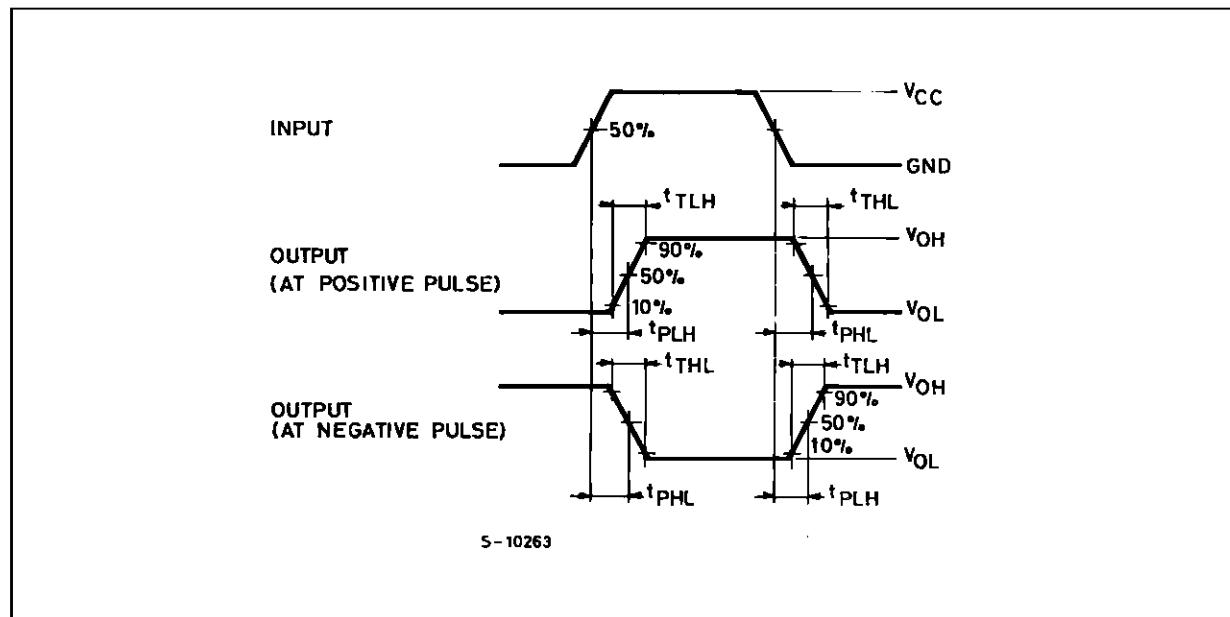
**DC SPECIFICATIONS**

Symbol	Parameter	Test Conditions		Value								Unit
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC			
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
V <sub>IH</sub>	High Level Input Voltage	2.0		1.5			1.5		1.5		V	
		4.5		3.15			3.15		3.15			
		6.0		4.2			4.2		4.2			
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.5		0.5		0.5	V	
		4.5				1.35		1.35		1.35		
		6.0				1.8		1.8		1.8		
V <sub>OH</sub>	High Level Output Voltage	2.0	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I <sub>O</sub> =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I <sub>O</sub> =-5.2 mA	5.68	5.8		5.63		5.60		
V <sub>OL</sub>	Low Level Output Voltage	2.0	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>O</sub> = 20 μA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I <sub>O</sub> = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I <sub>O</sub> = 5.2 mA		0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			±0.1		±1		±1	μA	
I <sub>CC</sub>	Quiescent Supply Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			4		40		80	μA	

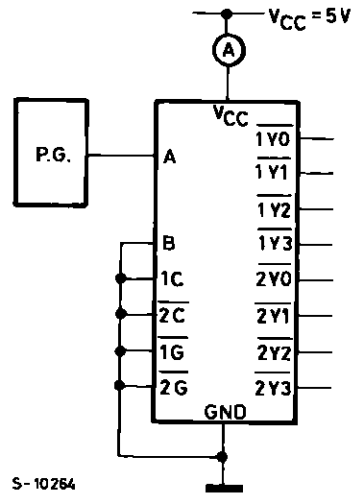
**AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ )

Symbol	Parameter	Test Conditions		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t <sub>TLH</sub> t <sub>THL</sub>	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	2.0			45	130		165		195	ns
		4.5			15	26		33		39	
		6.0			13	22		28		33	
C <sub>IN</sub>	Input Capacitance				5	10		10		10	pF
C <sub>PD</sub> (*)	Power Dissipation Capacitance				53						pF

(\*)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

**SWITCHING CHARACTERISTICS TEST WAVEFORM**

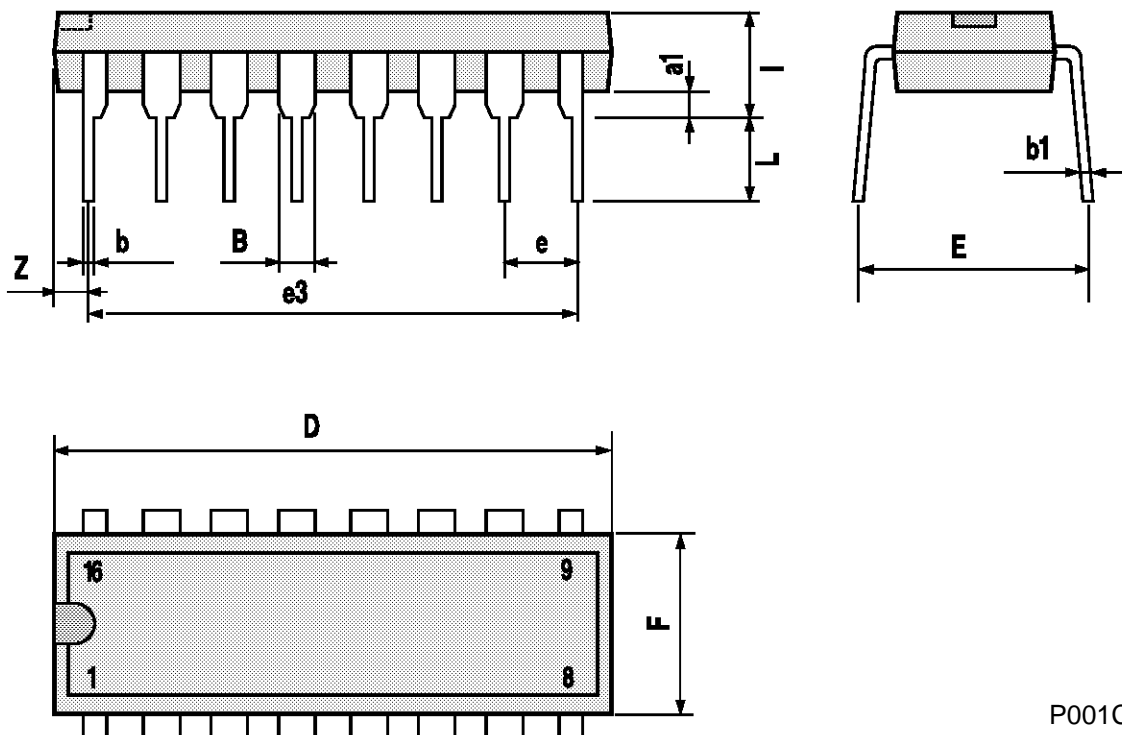
**TEST WAVEFORM  $I_{CC}$  (Opr.)**



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

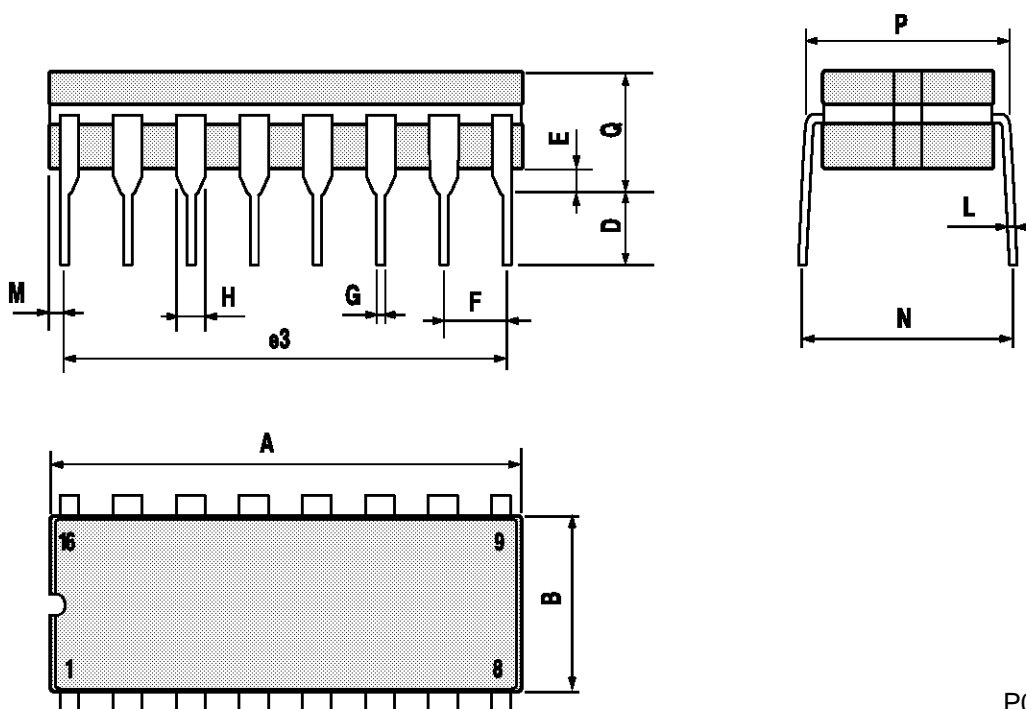
# Plastic DIP16 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



## Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200

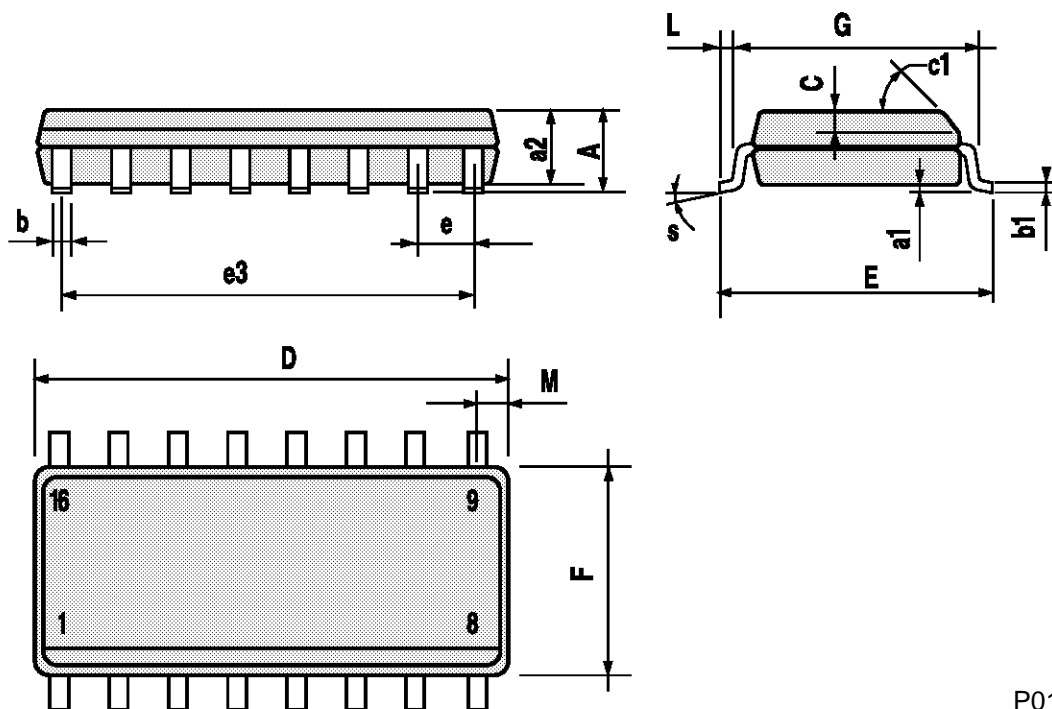


P053D



## SO16 (Narrow) MECHANICAL DATA

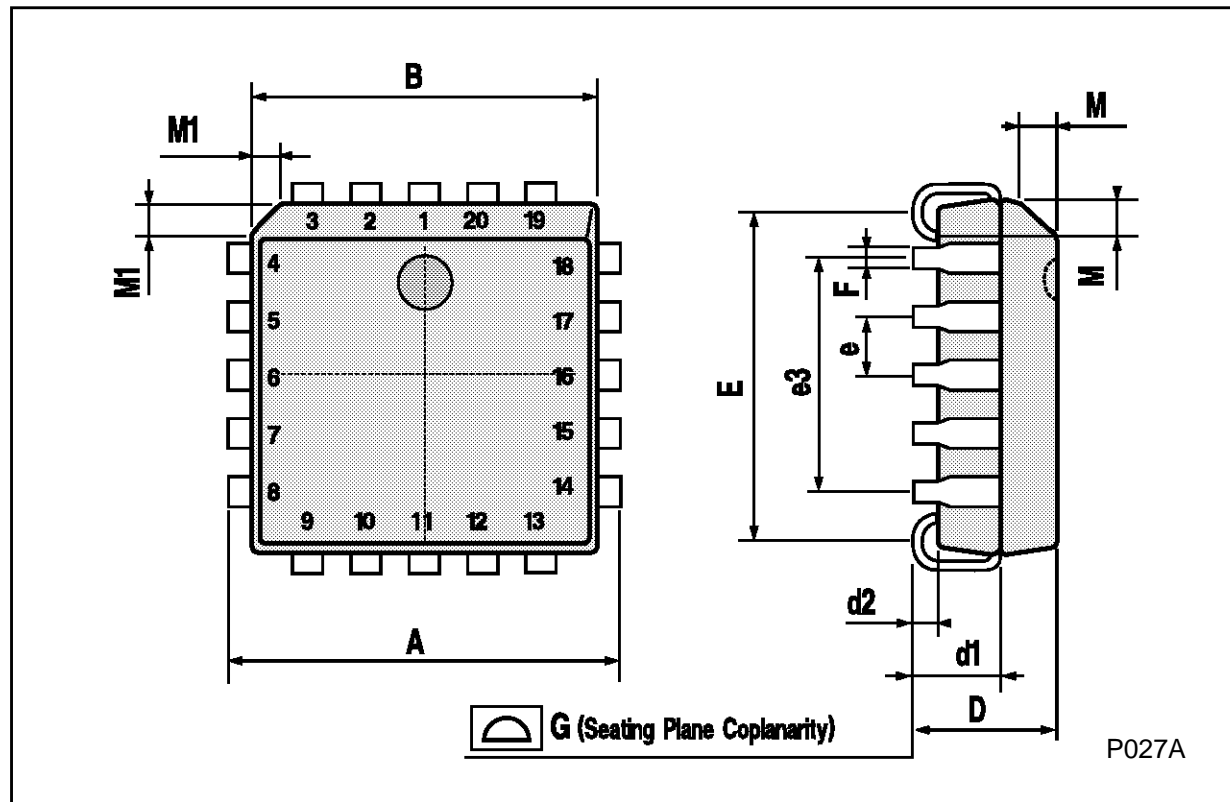
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

## PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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